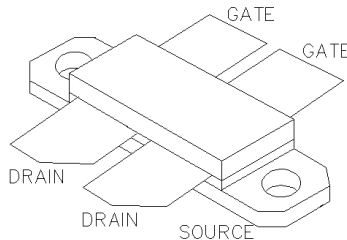




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.



SILICON GATE ENHANCEMENT MODE

RF POWER LDMOS TRANSISTOR

130.0 Watts Push - Pull

Package Style LB

**HIGH EFFICIENCY, LINEAR
HIGH GAIN, LOW NOISE**

ABSOLUTE MAXIMUM RATINGS (T = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
230 Watts	0.75 °C/W	200 °C	-65 °C to 150 °C	13.5 A	70V	70V	20 V

RF CHARACTERISTICS (130.0 WATTS OUTPUT)

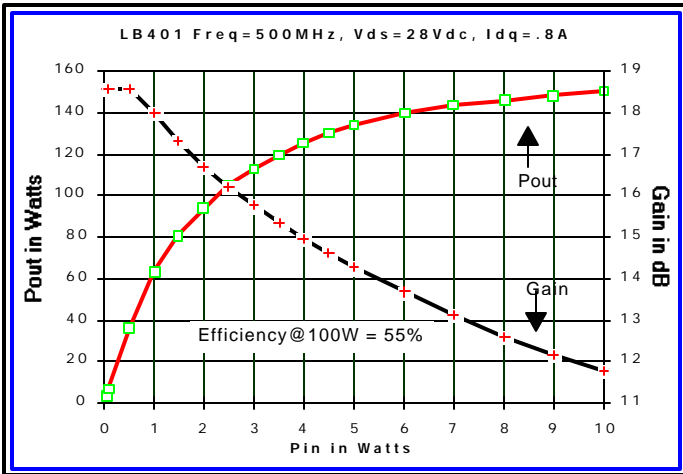
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	14			dB	Idq = 0.40 A, Vds = 28.0 V, F = 500MHz
η	Drain Efficiency		55		%	Idq = 0.40 A, Vds = 28.0 V, F = 500MHz
VSWR	Load Mismatch Tolerance			20:1	Relative	Idq = 0.40 A, Vds = 28.0 V, F = 500MHz

ELECTRICAL CHARACTERISTICS (EACH SIDE)

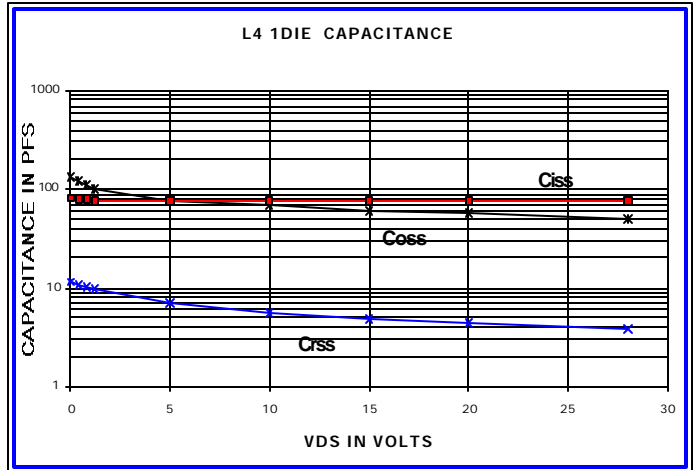
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	Ids = 0.25 mA, Vgs = 0V
Idss	Zero Bias Drain Current			1.0	mA	Vds = 28.0 V, Vgs = 0V
Igss	Gate Leakage Current			1	uA	Vds = 0V Vgs = 30V
Vgs	Gate Bias for Drain Current	1		7	V	Ids = 0.30 A, Vgs = Vds
gM	Forward Transconductance		2.7		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistance		0.28		Ohm	Vgs = 20V, Ids = 8.00 A
Idsat	Saturation Current		17.00		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitance		80.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitance		4.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitance		50.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz

LB401

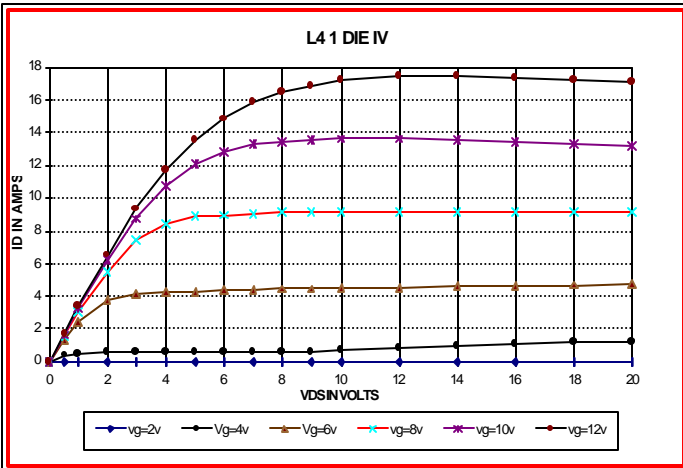
POUT VS PIN GRAPH



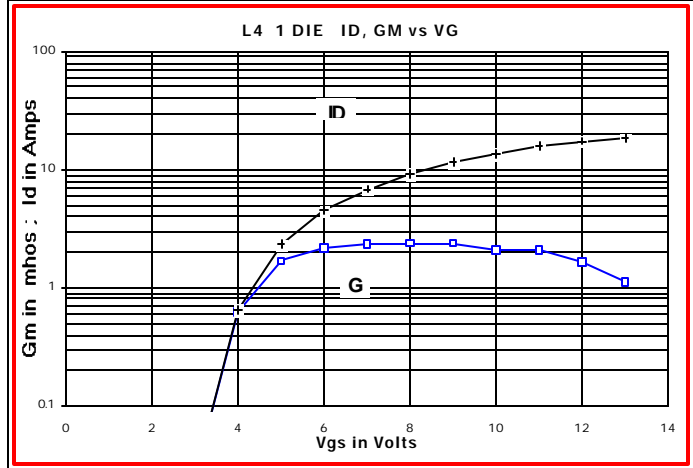
CAPACITANCE VS VOLTAGE



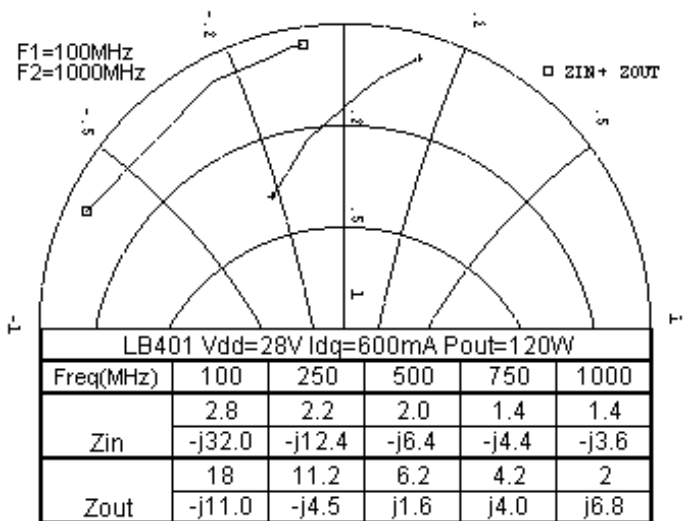
IV CURVE



ID & GM VS VGS



Zin Zout



PACKAGE DIMENSIONS IN INCHES

